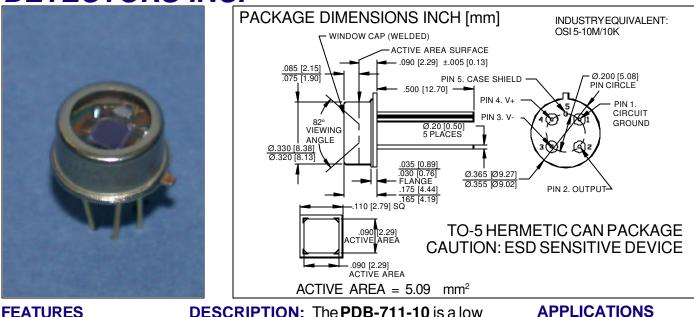
## PHOTONIC DETECTORS INC.

## **Detector Amplifier Hybrid, Blue Enhanced Type PDB-711-10**

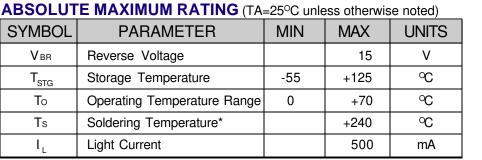


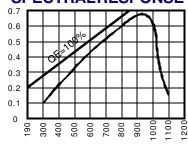
- 10 Khz bandwidth
- Internal10 MOhm gain
- Low offset voltage •
- Low input bias current

noise, medium speed, blue enhanced silicon photodiode integrated with a low noise JFET monolithic transimpedance op-amp. There is an internal 10 MOhm feedback gain resistor which limits the bandwidth to 10KHz.

- Medical diagnostic
- Low signal applications
- Color analysis
- Analytical chemistry

### **SPECTRALRESPONSE**





WAVELENGTH(nm)

RESPONSIVITY (A/W)

\*1/16 inch from case for 3 secs max

### PHOTODIODE ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TESTCONDITIONS	MIN	TYP	MAX	UNITS
lsc	Short Circuit Current	H = 100 fc, 2850 K	45	65		μA
ΙD	Dark Current	H = 0, V <sub>R</sub> = 10 V		1.0	5.0	nA
Rsh	Shunt Resistance	$H = 0, V_{R} = 10 \text{ mV}$	.5	2		GΩ
TC Rsh	RSH Temp. Coefficient	$H = 0, V_{R} = 10 \text{ mV}$		-8		% / °C
CJ	Junction Capacitance	$H = 0, V_{R} = 10 V^{**}$		15		pF
λrange	Spectral Application Range	Spot Scan	350		1100	nm
λρ	Spectral Response - Peak	Spot Scan		950		nm
VBR	Breakdown Voltage	I = 10 µµA	100	125		V
NEP	Noise Equivalent Power	VR = 10 V @ Peak		2.5x10 <sup>-14</sup>		W/ <del>V</del> Hz
tr	Response Time	$RL = 1 K\Omega V_R = 10 V$		15		nS

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications PAGE 1 OF 2 are subject to change without notice. \*\* f = 1 MHz [FORM NO. 100-PDB-711-10 REV A]

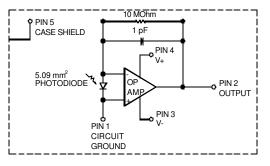
# PHOTONIC DETECTORS INC.

AMPLIFIER SPECIFICATION TA=25° C and VS=± 15 vdc UNLESS OTHERWISE NOTED

CHARACTERISTIC	TEST CONDITIONS	MIN	ТҮР	MAX	UNITS	
FEEDBACKNETWORK10 MEG $\Omega$ RESISTER,1pF* CAPACITOR	THINFILMRESISTOR TRIMMED TO±5% *TOL ±5%		10		MEG $\Omega$	
	INITIALOFFSET		0.75	2.0	mV	
INPUT OFFSET VOLTAGE	LONG TERM OFFSET STABILITY		15		μV/MONTH	
INPUT BIAS CURRENT	OFFSETCURRENT, VCM=0		5	20	рА	
INPUT IMPEDANCE	DIFFERENTIAL		1 X 10 <sup>-12</sup> 3		Ω∥pF	
	COMMONMODE		1 X 10 <sup>-12</sup> ∥3			
INPUT VOLTAGE RANGE	COMMONMODE	±11	±12		V	
INFUT VOLTAGE HANGE	COMMONMODE REJECTION VCM±10 V	76	90			
INPUT VOLTAGE NOISE	VOLTAGE 0, 1 Hz TO 10 Hz		2		μV р-р	
INFUT VOLTAGENOISE	VOLTAGE 0, f=10 Khz		30		nV∕√Hz	
INPUT CURRENTNOISE	f=1 Khz		1.8		fA / $\sqrt{Hz}$	
FREQUENCY RESPONSE	UNITY GAIN, SMALL SIGNAL	0.8	1.0		MHz	
FREQUENCE RESPONSE	SLEW RATE, UNITY GAIN	1.0	1.8		V/µs	
OPEN LOOP GAIN	vo= $\pm 10$ V, R <sub>L</sub> =10 K $\Omega$	300	1000		V/mV	
OUTPUT CHARACTERISTICS	VOLTAGE @ $R_L=10 K\Omega$	±12	±13		V	
	VOLTAGE @ $R_1 > 5K\Omega$	±11	±12.3		V	
POWER SUPPLY	OPERATING RANGE	±4.5	±15	±18	V	

AMPLIFIER ABSOLUTE MAXIMUM RATING (TA=25°C UNLESS OTHERWISE NOTED)

PARAMETER	MIN	MAX	UNITS
SUPPLYVOLTAGE	±4.5	±18	V
INTERNAL POWER DISSIPATION		500	mW
STORAGETEMPERATURE	-55	+150	° C
OPERATINGTEMPERATURE	0	+70	° C



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